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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	54
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 20x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl17z128vlh4r

Operating Characteristics

- Voltage range: 1.71 to 3.6 V
- Flash write voltage range: 1.71 to 3.6 V
- Temperature range: –40 to 85 °C for WLCSP package and –40 to 105 °C for other packages

Packages

- 64 LQFP 10mm x 10mm, 0.5mm pitch, 1.6mm thickness
- 64 MAPBGA 5mm x 5mm, 0.5mm pitch, 1.23mm thickness
- 48 QFN 7mm x 7mm, 0.5mm pitch, 0.65mm thickness
- 32 QFN 5mm x 5mm, 0.5mm pitch, 0.65mm thickness
- 36 WLCSP 2.8mm x 2.7mm, 0.4mm pitch, 0.6mm thickness

Security and Integrity

- 80-bit unique identification number per chip
- Advanced flash security

I/O

- Up to 54 general-purpose input/output pins (GPIO) and 6 high-drive pad

Low Power

- Down to 54uA/MHz in very low power run mode
- Down to 1.96uA in VLLS3 mode (RAM + RTC retained)
- Six flexible static modes

Ordering Information

Product		Memory		Package		IO and ADC channel		
Part number	Marking (Line1/ Line2)	Flash (KB)	SRAM (KB)	Pin count	Package	GPIOs	GPIOs (INT/HD)[1]	ADC channels (SE/DP)
MKL17Z128VFM4	M17P7V	128	32	32	QFN	28	19/6	11/2
MKL17Z256VFM4	M17P8V	256	32	32	QFN	28	19/6	11/2
MKL17Z128VFT4	M17P7V	128	32	48	QFN	40	24/6	18/3
MKL17Z256VFT4	M17P8V	256	32	48	QFN	40	24/6	18/3
MKL17Z128VLH4	MKL17Z128V//LH4	128	32	64	LQFP	54	31/6	20/4
MKL17Z256VLH4	MKL17Z256V//LH4	256	32	64	LQFP	54	31/6	20/4
MKL17Z128VMP4	M17P7V	128	32	64	MAPBGA	54	31/6	20/4
MKL17Z256VMP4	M17P8V	256	32	64	MAPBGA	54	31/6	20/4
MKL17Z256CAL4R	MKL17Z256CAL4	256	32	36	WLCSP	26	23/6	7/0

1. INT: interrupt pin numbers; HD: high drive pin numbers

Related Resources

Type	Description	Resource
Selector Guide	The Freescale Solution Advisor is a web-based tool that features interactive application wizards and a dynamic product selector.	Solution Advisor
Product Brief	The Product Brief contains concise overview/summary information to enable quick evaluation of a device for design suitability.	KL1XPB[1]
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.	KL17P64M48SF6RM[1]
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.	This document.
Chip Errata	The chip mask set Errata provides additional or corrective information for a particular device mask set.	KINETIS_L_1N71K[1]

Table continues on the next page...

1.4 Voltage and current operating ratings

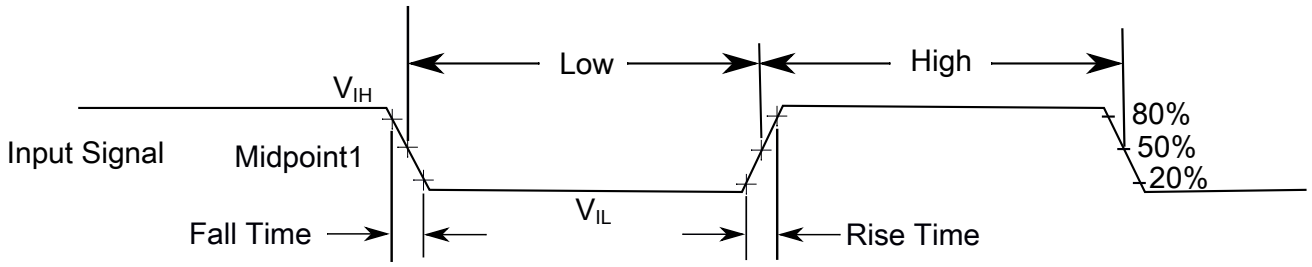
Table 4. Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	120	mA
V_{IO}	IO pin input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V

2 General

2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.



The midpoint is V_{IL} + (V_{IH} - V_{IL}) / 2

Figure 1. Input signal measurement reference

All digital I/O switching characteristics, unless otherwise specified, assume that the output pins have the following characteristics.

- C_L=30 pF loads
- Slew rate disabled
- Normal drive strength

2.2 Nonswitching electrical specifications

Table 8. Power mode transition operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• VLPS → RUN	—	7.5	8	µs	
	• STOP → RUN	—	7.5	8	µs	

1. Normal boot (FTFA_FOPT[LPBOOT]=11)

2.2.5 Power consumption operating behaviors

The maximum values stated in the following table represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

NOTE

The while (1) test is executed with flash cache enabled.

NOTE

The data at 105 °C are for QFN, LQFP and MAPBGA packages only.

Table 9. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUNCO}	Running CoreMark in flash in compute operation mode—48M HIRC mode, 48 MHz core / 24 MHz flash, V_{DD} = 3.0 V					2
	• at 25 °C	—	5.76	6.40	mA	
	• at 105 °C	—	6.04	6.68		
I_{DD_RUNCO}	Running While(1) loop in flash in compute operation mode—48M HIRC mode, 48 MHz core / 24 MHz flash, V_{DD} = 3.0 V					
	• at 25 °C	—	3.21	3.85	mA	
	• at 105 °C	—	3.49	4.13		
I_{DD_RUN}	Run mode current—48M HIRC mode, running CoreMark in Flash all peripheral clock disable 48 MHz core/24 MHz flash, V_{DD} = 3.0 V					2
	• at 25 °C	—	6.45	7.09	mA	
	• at 105 °C	—	6.75	7.39		
I_{DD_RUN}	Run mode current—48M HIRC mode, running CoreMark in flash all peripheral clock disable, 24 MHz core/12 MHz flash, V_{DD} = 3.0 V					2

Table continues on the next page...

Table 9. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• at 25 °C	—	3.95	4.59		
	• at 105 °C	—	4.23	4.87	mA	
I_{DD_RUN}	Run mode current—48M HIRC mode, running CoreMark in Flash all peripheral clock disable 12 MHz core/6 MHz flash, V_{DD} = 3.0 V					2
	• at 25 °C	—	2.68	3.32	mA	
	• at 105 °C	—	2.96	3.60		
I_{DD_RUN}	Run mode current—48M HIRC mode, running CoreMark in Flash all peripheral clock enable 48 MHz core/24 MHz flash, V_{DD} = 3.0 V					2
	• at 25 °C	—	8.08	8.72	mA	
	• at 105 °C	—	8.39	9.03		
I_{DD_RUN}	Run mode current—48M HIRC mode, running While(1) loop in flash all peripheral clock disable, 48 MHz core/24 MHz flash, V_{DD} = 3.0 V					
	• at 25 °C	—	3.90	4.54	mA	
	• at 105 °C	—	4.21	4.85		
I_{DD_RUN}	Run mode current—48M HIRC mode, running While(1) loop in Flash all peripheral clock disable, 24 MHz core/12 MHz flash, V_{DD} = 3.0 V					
	• at 25 °C	—	2.66	3.30	mA	
	• at 105 °C	—	2.94	3.58		
I_{DD_RUN}	Run mode current—48M HIRC mode, Running While(1) loop in Flash all peripheral clock disable, 12 MHz core/6 MHz flash, V_{DD} = 3.0 V					
	• at 25 °C	—	2.03	2.67	mA	
	• at 105 °C	—	2.31	2.95		
I_{DD_RUN}	Run mode current—48M HIRC mode, Running While(1) loop in Flash all peripheral clock enable, 48 MHz core/24 MHz flash, V_{DD} = 3.0 V					
	• at 25 °C	—	5.52	6.16	mA	
	• at 105 °C	—	5.83	6.47		
I_{DD_RUN}	Run mode current—48M HIRC mode, running While(1) loop in SRAM all peripheral clock disable, 48 MHz core/24 MHz flash, V_{DD} = 3.0 V					
	• at 25 °C	—	5.29	5.93	mA	
	• at 105 °C	—	5.56	6.20		
I_{DD_RUN}	Run mode current—48M HIRC mode, running While(1) loop in SRAM all peripheral clock enable, 48 MHz core/24 MHz flash, V_{DD} = 3.0 V					
		—	6.91	7.55	mA	
		—	7.19	7.91		

Table continues on the next page...

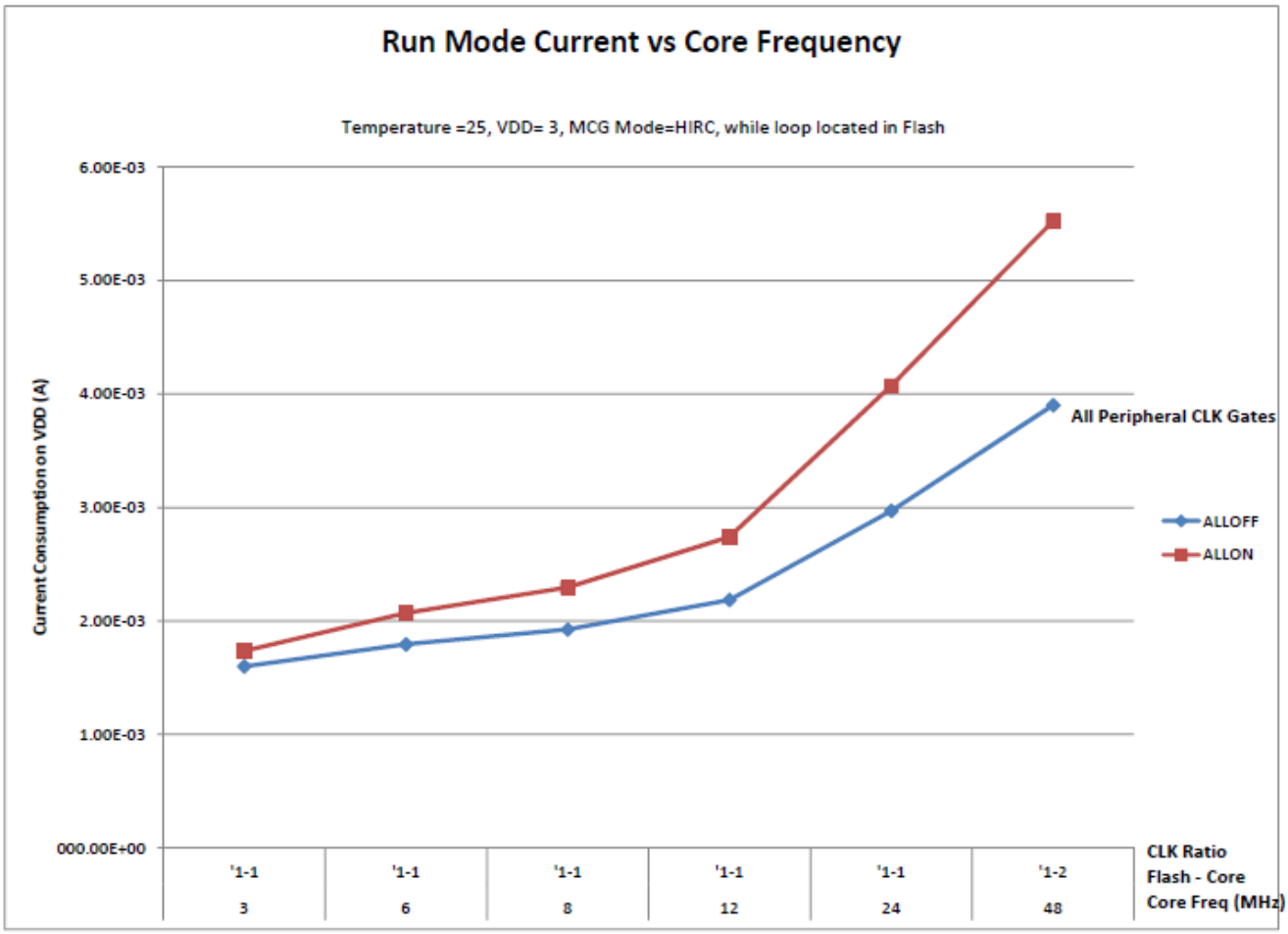


Figure 2. Run mode supply current vs. core frequency

of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

2. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = IRC48M, f_{SYS} = 48 MHz, f_{BUS} = 24 MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

2.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for "EMC design."

2.2.8 Capacitance attributes

Table 12. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN}	Input capacitance	—	7	pF

2.3 Switching specifications

2.3.1 Device clock specifications

Table 13. Device clock specifications

Symbol	Description	Min.	Max.	Unit
Normal run mode				
f_{SYS}	System and core clock[1]	—	48	MHz
f_{BUS}	Bus clock[1]	—	24	MHz
f_{FLASH}	Flash clock[1]	—	24	MHz
f_{LPTMR}	LPTMR clock	—	24	MHz
VLPR and VLPS modes[2]				
f_{SYS}	System and core clock	—	4	MHz
f_{BUS}	Bus clock	—	1	MHz
f_{FLASH}	Flash clock	—	1	MHz
f_{LPTMR}	LPTMR clock[3]	—	24	MHz

Table continues on the next page...

1. Maximum T_A can be exceeded only if the user ensures that T_J does not exceed the maximum. The simplest method to determine T_J is: $T_J = T_A + R_{\theta JA} \times$ chip power dissipation.

Table 16. Thermal operating requirements for other packages

Symbol	Description	Min.	Max.	Unit	Notes
T_J	Die junction temperature	–40	125	°C	
T_A	Ambient temperature	–40	105	°C	1

1. Maximum T_A can be exceeded only if the user ensures that T_J does not exceed the maximum. The simplest method to determine T_J is: $T_J = T_A + R_{\theta JA} \times$ chip power dissipation.

2.4.2 Thermal attributes

Table 17. Thermal attributes

Board type	Symbol	Description	48 QFN	32 QFN	64 LQFP	64 MAPBGA	36 WLCSP	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	86	101	70	50.3	77.6	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	29	33	51	42.9	38.9	°C/W	
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	71	84	58	41.4	69.6	°C/W	
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	24	28	45	38.0	35.6	°C/W	
—	$R_{\theta JB}$	Thermal resistance, junction to board	12	13	33	39.6	34.8	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	1.7	1.7	20	27.3	0.37	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	2	3	4	0.4	0.2	°C/W	4
—	Ψ_{JB}	Thermal characterization parameter, junction to package bottom (natural convection)	-	-	-	12.6	-	°C/W	5

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.

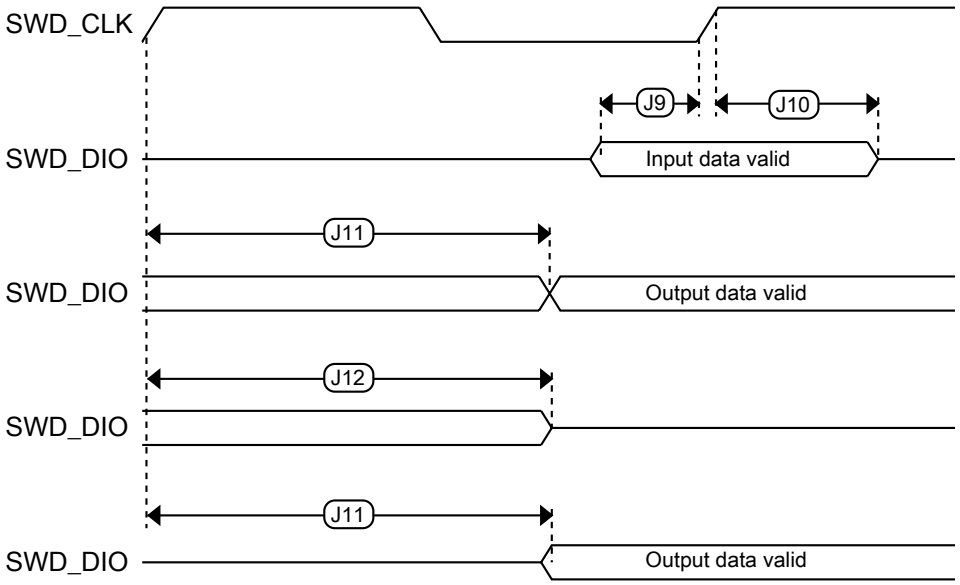


Figure 5. Serial wire data timing

3.2 System modules

There are no specifications necessary for the device's system modules.

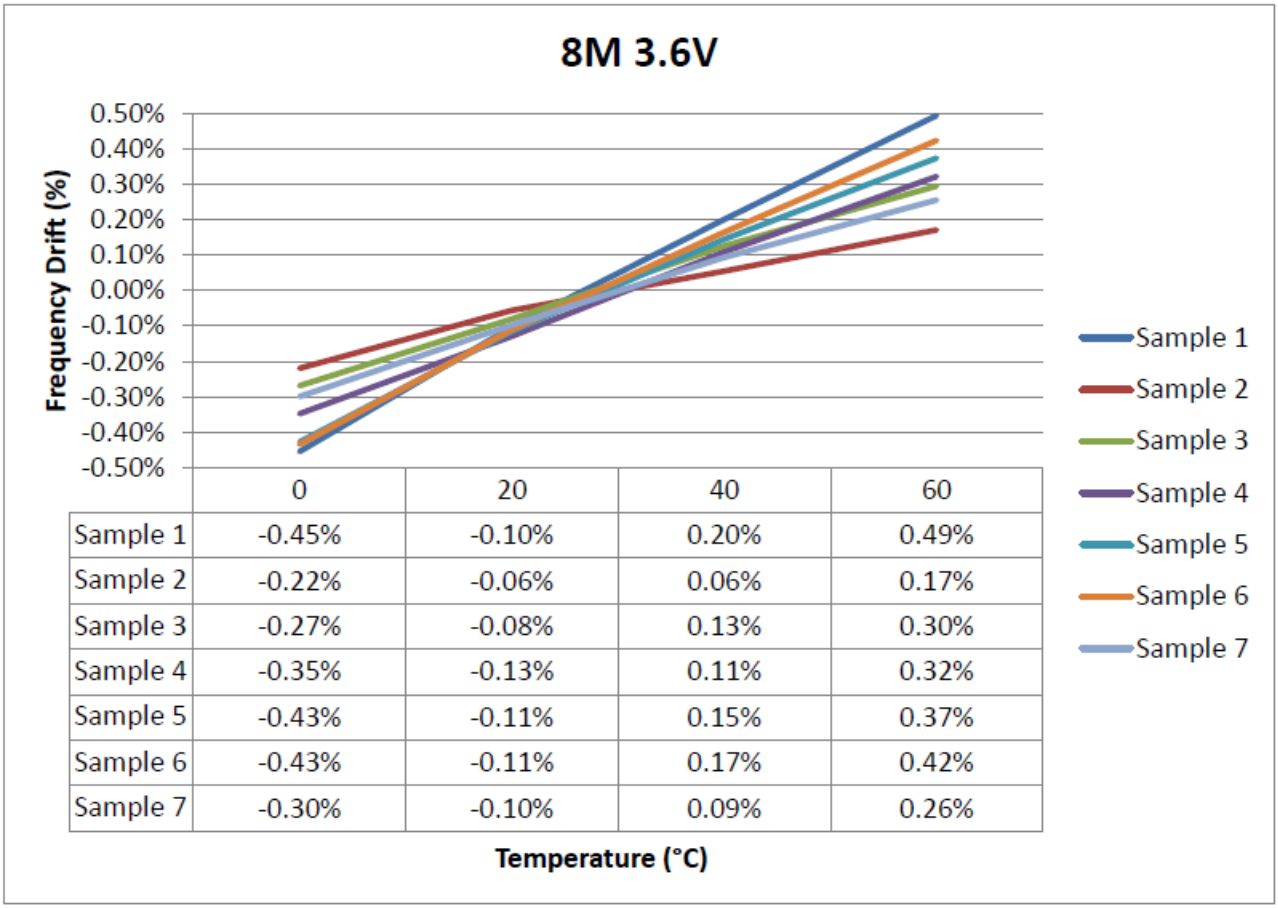
3.3 Clock modules

3.3.1 MCG-Lite specifications

Table 19. IRC48M specification

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD}	Supply current	—	400	500	µA	—
f_{IRC}	Output frequency	—	48	—	MHz	—
$\Delta f_{irc48m\_ol\_lv}$	Open loop total deviation of IRC48M frequency at low voltage (VDD=1.71V-1.89V) over temperature	—	± 0.5	± 1.5	$\%f_{irc48m}$	1
$\Delta f_{irc48m\_ol\_hv}$	Open loop total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over temperature	—	± 0.5	± 1.0	$\%f_{irc48m}$	1

Table continues on the next page...



	0	20	40	60
Sample 1	-0.45%	-0.10%	0.20%	0.49%
Sample 2	-0.22%	-0.06%	0.06%	0.17%
Sample 3	-0.27%	-0.08%	0.13%	0.30%
Sample 4	-0.35%	-0.13%	0.11%	0.32%
Sample 5	-0.43%	-0.11%	0.15%	0.37%
Sample 6	-0.43%	-0.11%	0.17%	0.42%
Sample 7	-0.30%	-0.10%	0.09%	0.26%

Figure 6. IRC8M Frequency Drift vs Temperature curve

3.3.2 Oscillator electrical specifications

3.3.2.1 Oscillator DC electrical specifications

Table 21. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 4 MHz	—	200	—	µA	
	• 8 MHz (RANGE=01)	—	300	—	µA	
	• 16 MHz	—	950	—	µA	
		—	1.2	—	mA	

Table continues on the next page...

Table 21. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• 24 MHz • 32 MHz	—	1.5	—	mA	
I_{DDOSC}	Supply current — high gain mode (HGO=1)					1
	• 32 kHz	—	25	—	µA	
	• 4 MHz	—	400	—	µA	
	• 8 MHz (RANGE=01)	—	500	—	µA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V_{pp}[5]	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation

3. C_x,C_y can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

3.3.2.2 Oscillator frequency specifications

Table 22. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low-frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc\_hi\_1}$	Oscillator crystal or resonator frequency — high-frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	48	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL
2. When transitioning from FEI or FBI to FBE mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

3.4 Memories and memory interfaces

3.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

3.4.1.3 Flash high voltage current behaviors

Table 25. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 26. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	—
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	—
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at –40 °C ≤ T_j ≤ 125 °C.

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 ADC electrical specifications

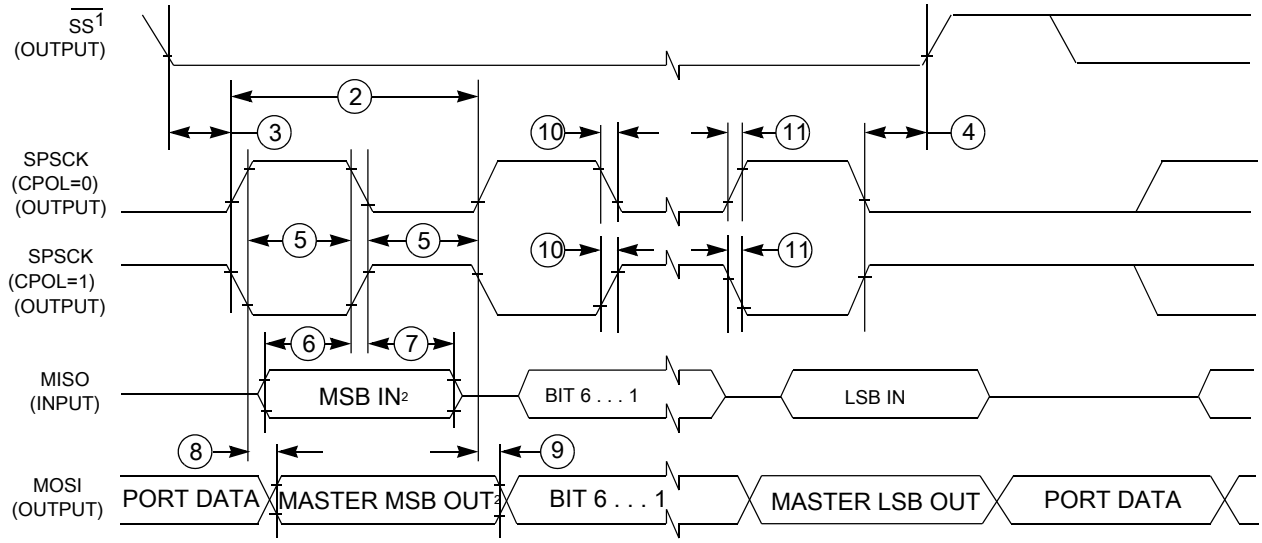
Using differential inputs can achieve better system accuracy than using single-end inputs.

3.6.1.1 16-bit ADC operating conditions

Table 27. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	—
ΔV_{DDA}	Supply voltage	Delta to V_{DD} ($V_{DD} - V_{DDA}$)	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} ($V_{SS} - V_{SSA}$)	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	3
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	3
V_{ADIN}	Input voltage	• 16-bit differential mode • All other modes	VREFL VREFL	— —	31/32 × VREFH VREFH	V	—
C_{ADIN}	Input capacitance	• 16-bit mode • 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	—
R_{ADIN}	Input series resistance		—	2	5	kΩ	—
R_{AS}	Analog source resistance (external)	13-bit / 12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	4
f_{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	24	MHz	5
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	5
C_{rate}	ADC conversion rate	≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	1200	ksps	6
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	ksps	6

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. VREFH can act as VREF_OUT when VREFV1 module is enabled.
4. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
5. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
6. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.



1.If configured as output

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 15. SPI master mode timing (CPHA = 1)

Table 38. SPI slave mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCK}	SPSCK period	4 x t_{periph}	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	—	ns	—
6	t_{SU}	Data setup time (inputs)	2.5	—	ns	—
7	t_{HI}	Data hold time (inputs)	3.5	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCK edge)	—	31	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	t_{periph} - 25	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
2. $t_{periph} = 1/f_{periph}$
3. Time to data active from high-impedance state
4. Hold time to high-impedance state

Table 39. SPI slave mode timing on slew rate enabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCK}	SPSCK period	4 x t_{periph}	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	—	ns	—
6	t_{SU}	Data setup time (inputs)	2	—	ns	—
7	t_{HI}	Data hold time (inputs)	7	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCK edge)	—	122	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	t_{periph} - 25	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
2. $t_{periph} = 1/f_{periph}$
3. Time to data active from high-impedance state
4. Hold time to high-impedance state

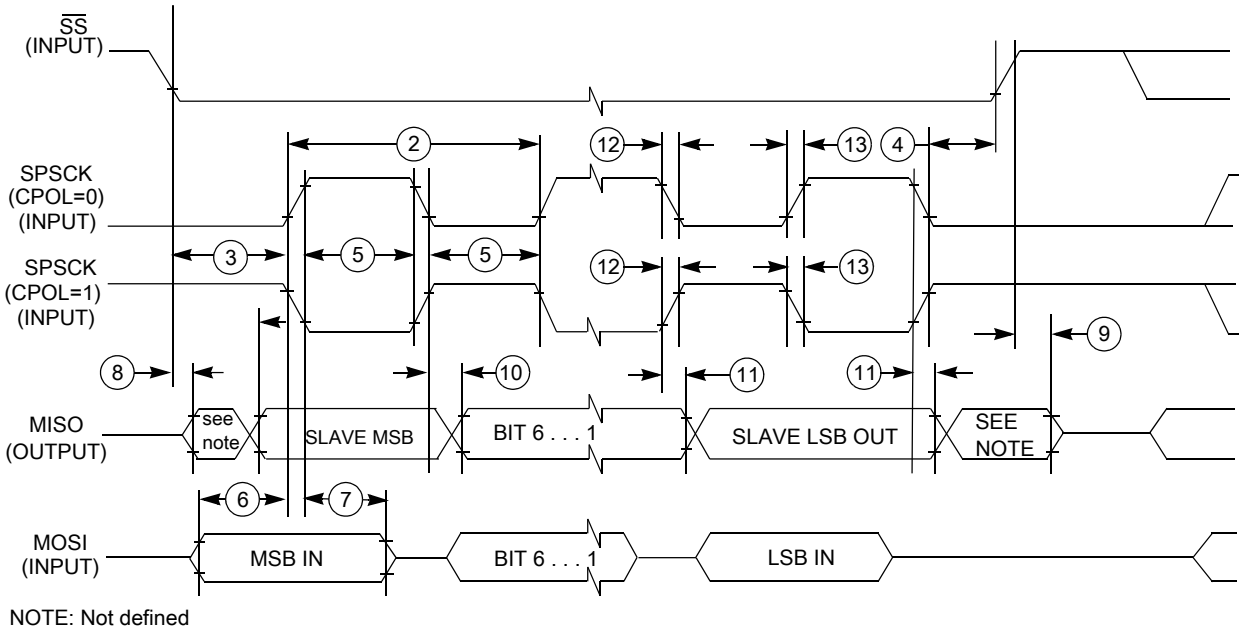


Figure 16. SPI slave mode timing (CPHA = 0)

3.8.3 UART

See General switching specifications.

3.8.4 I2S/SAI switching specifications

This section provides the AC timing for the I2S/SAI module in master mode (clocks are driven) and slave mode (clocks are input). All timing is given for noninverted serial clock polarity (TCR2[BCP] is 0, RCR2[BCP] is 0) and a noninverted frame sync (TCR4[FSP] is 0, RCR4[FSP] is 0). If the polarity of the clock and/or the frame sync have been inverted, all the timing remains valid by inverting the bit clock signal (BCLK) and/or the frame sync (FS) signal shown in the following figures.

3.8.4.1 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Table 42. I2S/SAI master mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK (as an input) pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15.5	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	19	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	26	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

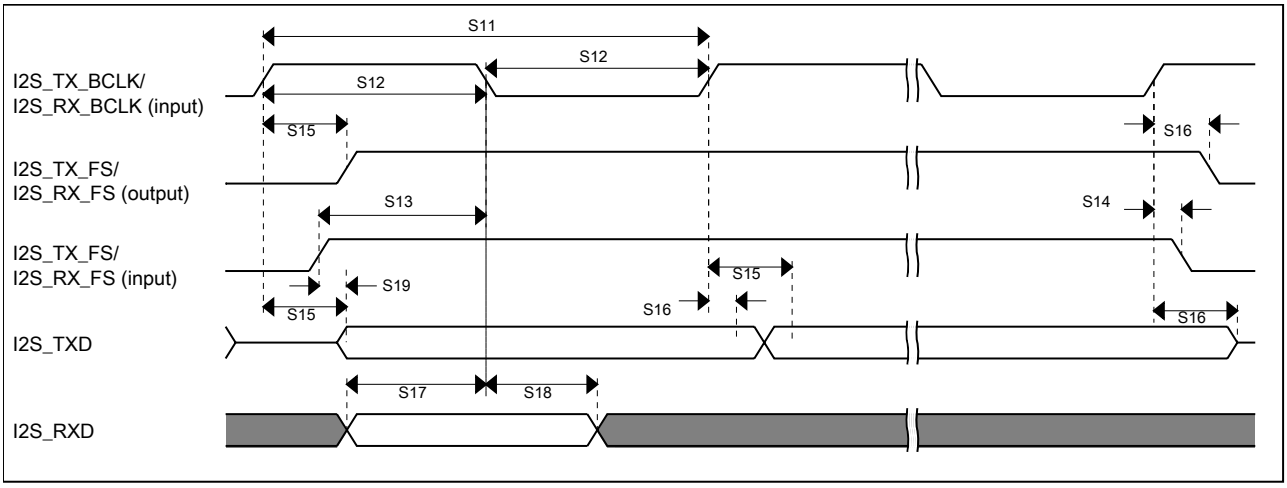


Figure 22. I2S/SAI timing — slave modes

4 Dimensions

4.1 Obtaining package dimensions

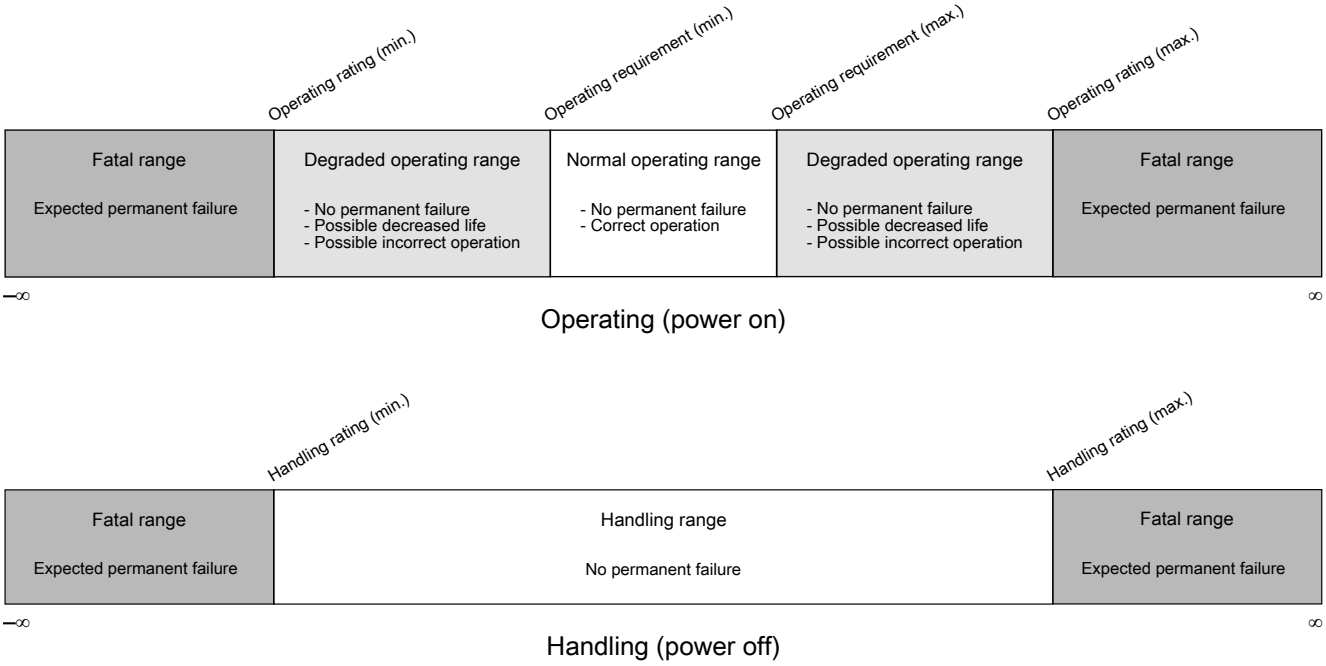
Package dimensions are provided in package drawings.

To find a package drawing, go to freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
32-pin QFN	98ASA00615D
36-pin WLCSP	98ASA00949D
48-pin QFN	98ASA00616D
64-pin LQFP	98ASS23234W
64-pin MAPBGA	98ASA00420D

64 MAP BGA	64 LQFP	48 QFN	36 WLCSP	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
E8	38	30	—	—	PTB3	ADC0_SE13	ADC0_SE13	PTB3	I2C0_SDA	TPM2_CH1				
E6	39	31	—	—	PTB16	DISABLED		PTB16	SPI1_MOSI	LPUART0_RX	TPM_CLKIN0	SPI1_MISO		
D7	40	32	—	—	PTB17	DISABLED		PTB17	SPI1_MISO	LPUART0_TX	TPM_CLKIN1	SPI1_MOSI		
D6	41	—	—	—	PTB18	DISABLED		PTB18		TPM2_CH0	I2S0_TX_BCLK			
C7	42	—	—	—	PTB19	DISABLED		PTB19		TPM2_CH1	I2S0_TX_FS			
D8	43	33	—	—	PTC0	ADC0_SE14	ADC0_SE14	PTC0		EXTRG_IN	audioUSB_SOF_OUT	CMP0_OUT	I2S0_TXD0	
C6	44	34	B1	22	PTC1/LLWU_P6/RTC_CLKIN	ADC0_SE15	ADC0_SE15	PTC1/LLWU_P6/RTC_CLKIN	I2C1_SCL		TPM0_CH0		I2S0_TXD0	
B7	45	35	B2	23	PTC2	ADC0_SE11	ADC0_SE11	PTC2	I2C1_SDA		TPM0_CH1		I2S0_TX_FS	
C8	46	36	A1	24	PTC3/LLWU_P7	DISABLED		PTC3/LLWU_P7	SPI1_SCK	LPUART1_RX	TPM0_CH2	CLKOUT	I2S0_TX_BCLK	
E3	47	—	C4	—	VSS	VSS	VSS							
E4	48	—	B3	—	VDD	VDD	VDD							
B8	49	37	A2	25	PTC4/LLWU_P8	DISABLED		PTC4/LLWU_P8	SPI0_PCS0	LPUART1_TX	TPM0_CH3	I2S0_MCLK		
A8	50	38	A3	26	PTC5/LLWU_P9	DISABLED		PTC5/LLWU_P9	SPI0_SCK	LPTMR0_ALT2	I2S0_RXD0		CMP0_OUT	
A7	51	39	B4	27	PTC6/LLWU_P10	CMP0_IN0	CMP0_IN0	PTC6/LLWU_P10	SPI0_MOSI	EXTRG_IN	I2S0_RX_BCLK	SPI0_MISO	I2S0_MCLK	
B6	52	40	A4	28	PTC7	CMP0_IN1	CMP0_IN1	PTC7	SPI0_MISO	audioUSB_SOF_OUT	I2S0_RX_FS	SPI0_MOSI		
A6	53	—	—	—	PTC8	CMP0_IN2	CMP0_IN2	PTC8	I2C0_SCL	TPM0_CH4	I2S0_MCLK			
B5	54	—	—	—	PTC9	CMP0_IN3	CMP0_IN3	PTC9	I2C0_SDA	TPM0_CH5	I2S0_RX_BCLK			
B4	55	—	—	—	PTC10	DISABLED		PTC10	I2C1_SCL		I2S0_RX_FS			
A5	56	—	—	—	PTC11	DISABLED		PTC11	I2C1_SDA		I2S0_RXD0			
C3	57	41	—	—	PTD0	DISABLED		PTD0	SPI0_PCS0		TPM0_CH0		FXIO0_D0	
A4	58	42	—	—	PTD1	ADC0_SE5b	ADC0_SE5b	PTD1	SPI0_SCK		TPM0_CH1		FXIO0_D1	
C2	59	43	—	—	PTD2	DISABLED		PTD2	SPI0_MOSI	UART2_RX	TPM0_CH2	SPI0_MISO	FXIO0_D2	
B3	60	44	—	—	PTD3	DISABLED		PTD3	SPI0_MISO	UART2_TX	TPM0_CH3	SPI0_MOSI	FXIO0_D3	
A3	61	45	A5	29	PTD4/LLWU_P14	DISABLED		PTD4/LLWU_P14	SPI1_PCS0	UART2_RX	TPM0_CH4		FXIO0_D4	
C1	62	46	B5	30	PTD5	ADC0_SE6b	ADC0_SE6b	PTD5	SPI1_SCK	UART2_TX	TPM0_CH5		FXIO0_D5	
B2	63	47	A6	31	PTD6/LLWU_P15	ADC0_SE7b	ADC0_SE7b	PTD6/LLWU_P15	SPI1_MOSI	LPUART0_RX		SPI1_MISO	FXIO0_D6	

8.4 Relationship between ratings and operating requirements



8.5 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

9 Revision History

The following table provides a revision history for this document.

Table 48. Revision History

Rev. No.	Date	Substantial Changes
3	09 August 2014	Initial Public release • Updated Table 9 - Power consumption operating behaviors. • Added a note related to 32 QFN pin package in Pinouts topic.
4	03 March 2015	• Updated the features and completed the ordering information. • Removed thickness dimension from package diagrams.

Table continues on the next page...

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